

深圳市晶泰源电子有限公司

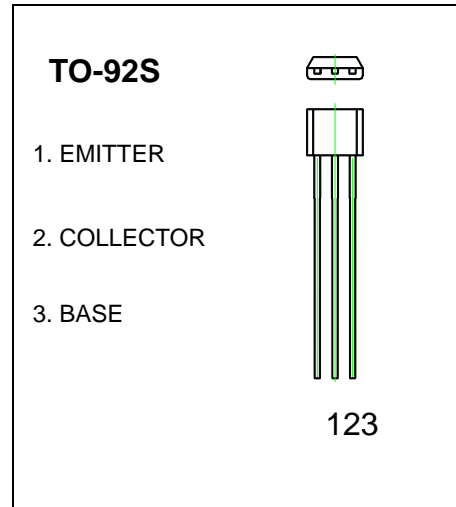
2SA1585S TRANSISTOR (PNP)

FEATURES

- LOW $V_{CE(sat)} \cdot V_{CE(sat)} = 0.2V$ (Typ.) ($I_C/I_B = 2A/0.1A$)
- Excellent DC current gain characteristics.
- Power dissipation

MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-20	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power Dissipation	400	mW
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55-150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -0.1A$	120		560	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -2A, I_B = -0.1A$			-0.5	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -0.5A$ $F = 100MHz$	200			MHz

CLASSIFICATION OF h_{FE}

Rank	Q	R	s
Range	120-170	180-390	270-560